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Attorney Docket: P-1164-US2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Boaz EITAN

Examiner:

C. Chaudhari

Serial No.: 09/966,754

Group Art Unit:

2813

Filed: July 30, 1999

Title: AN NROM FABRICATION METHOD

AMENDMENT

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APR 03 2002

Assistant Commissioner for Patents
Washington, DC 20231

Technology Center 2100

Sir:

This Amendment is filed in response to the Office Action dated February 26, 2002 issued by the United States Patent and Trademark Office in connection with the above-identified Application. A response to the February 26, 2002 Office Action is due May 26, 2002. Accordingly, this Amendment is being timely filed.

Kindly amend the above-identified application as follows:

In the Claims

Kindly amend claims 1, 4 and 5 to read as follows.

1. A method of fabricating an oxide-nitride-oxide (ONO) layer in a memory cell, said method comprising:

forming a bottom oxide layer on a substrate;

depositing a nitride layer; and

oxidizing a top oxide layer, thereby causing oxygen to be introduced into generally all of said nitride layer within said memory cell.

4. A method for improving the charge retention in a nitride layer of a memory cell, said method comprising: